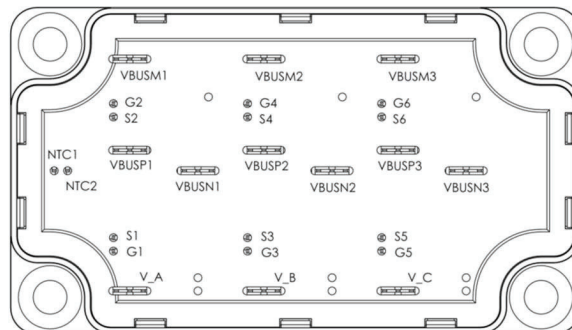
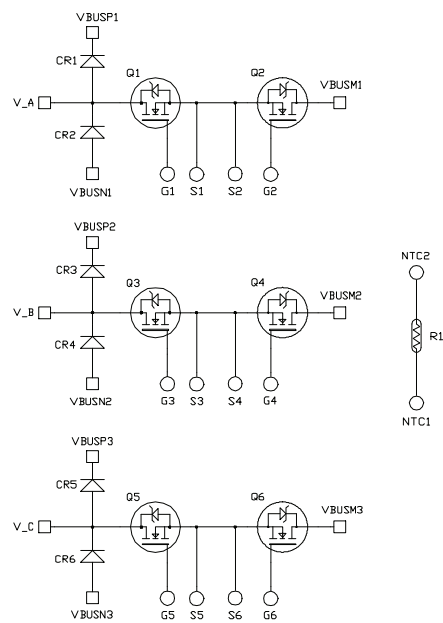


## Triple Vienna Rectifier SiC MOSFET Power Module

### Product Overview

The MSCSM70VR1M10CTPAG device is a triple Vienna rectifier 700V, 238A silicon carbide (SiC) power module.



**Note:** All ratings at  $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise specified.



These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

## Features

The following are the key features of MSCSM70VR1M10CTPAG device:

- SiC Power MOSFET
  - Low  $R_{DS(on)}$
  - High temperature performance
- SiC Schottky Diode
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature independent switching behavior
  - Positive temperature coefficient on  $V_F$
- Very low stray inductance
- Internal thermistor for temperature monitoring
- Kelvin source for easy drive
- Aluminum Nitride (AlN) substrate for improved thermal performance

## Benefits

The following are the benefits of MSCSM70VR1M10CTPAG device:

- Outstanding performance at high frequency operation
- High-power and high-efficiency rectifiers and converters
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

## Applications

The following are the applications of MSCSM70VR1M10CTPAG device:

- Power factor correction
- Switched mode power supplies
- Uninterruptible power supplies

## 1. Electrical Specifications

The following sections show the electrical specifications of the MSCSM70VR1M10CTPAG device.

### 1.1 SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings (per SiC MOSFET) of the MSCSM70VR1M10CTPAG device.

**Table 1-1. Absolute Maximum Ratings**

Symbol	Parameter		Maximum Ratings	Unit
$V_{DSS}$	Drain-Source voltage		700	V
$I_D$	Continuous drain current	$T_C = 25\text{ }^\circ\text{C}$	238 <sup>1</sup>	A
		$T_C = 80\text{ }^\circ\text{C}$	189 <sup>1</sup>	
$I_{DM}$	Pulsed drain current		480	
$V_{GS}$	Gate-Source voltage		-10/23	V
$R_{DS(on)}$	Drain-Source ON resistance		9.5	m $\Omega$
$P_D$	Power dissipation	$T_C = 25\text{ }^\circ\text{C}$	674	W

**Note:**

1. Specification of SiC MOSFET device but output current must be limited due to size of power connectors.

The following table lists the electrical characteristics (per SiC MOSFET) of the MSCSM70VR1M10CTPAG device.

**Table 1-2. Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0V; V_{DS} = 700V$	—	—	200	$\mu\text{A}$
$R_{DS(on)}$	Drain-Source on resistance	$V_{GS} = 20V$ $I_D = 80A$	—	7.5	9.5	m $\Omega$
		$T_J = 175\text{ }^\circ\text{C}$	—	9.5	—	
$V_{GS(th)}$	Gate threshold voltage	$V_{GS} = V_{DS}; I_D = 8\text{ mA}$	1.9	2.4	—	V
$I_{GSS}$	Gate-Source leakage current	$V_{GS} = 20V; V_{DS} = 0V$	—	—	200	nA

# MSCSM70VR1M10CTPAG

## Electrical Specifications

The following table lists the dynamic characteristics (per SiC MOSFET) of the MSCSM70VR1M10CTPAG device.

**Table 1-3. Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit	
$C_{iss}$	Input capacitance	$V_{GS} = 0V$	—	9000	—	pF	
$C_{oss}$	Output capacitance	$V_{DS} = 700V$	—	1020	—		
$C_{rss}$	Reverse transfer capacitance	$f = 1\text{ MHz}$	—	58	—		
$Q_g$	Total gate charge	$V_{GS} = -5V/20V$	—	430	—	nC	
$Q_{gs}$	Gate-source charge	$V_{Bus} = 470V$	—	116	—		
$Q_{gd}$	Gate-drain charge	$I_D = 80A$	—	70	—		
$T_{d(on)}$	Turn-on delay time	$V_{GS} = -5V/20V$	$T_J = 150\text{ }^\circ\text{C}$	—	40	—	ns
$T_r$	Rise time	$V_{Bus} = 400V$		—	35	—	
$T_{d(off)}$	Turn-off delay time	$I_D = 160A$		—	50	—	
$T_f$	Fall time	$R_{GON} = 13.5\Omega$ $R_{GOFF} = 2.4\Omega$		—	20	—	
$E_{on}$	Turn-on energy	$V_{GS} = -5V/20V$	$T_J = 150\text{ }^\circ\text{C}$	—	1090	—	$\mu\text{J}$
$E_{off}$	Turn-off energy	$V_{Bus} = 400V$ $I_D = 160A$ $R_{GON} = 13.5\Omega$ $R_{GOFF} = 2.4\Omega$	$T_J = 150\text{ }^\circ\text{C}$	—	372	—	
$R_{Gint}$	Internal gate resistance		—	2.8	—	$\Omega$	
$R_{thJC}$	Junction-to-case thermal resistance		—	—	0.222	$^\circ\text{C/W}$	

The following table lists the body diode ratings and characteristics (per SiC MOSFET) of the MSCSM70VR1M10CTPAG device.

**Table 1-4. Body Diode Ratings and Characteristics**

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
$V_{SD}$	Diode forward voltage	$V_{GS} = 0V; I_{SD} = 80A$	—	3.4	—	V
		$V_{GS} = -5V; I_{SD} = 80A$	—	3.8	—	
$t_{rr}$	Reverse recovery time	$I_{SD} = 80A$	—	38	—	ns
$Q_{rr}$	Reverse recovery charge	$V_{GS} = -5V$	—	636	—	nC
$I_{rr}$	Reverse recovery current	$V_R = 400V$ $di_F/dt = 2000\text{ A}/\mu\text{s}$	—	29.6	—	A

### 1.2 SiC Diode Ratings and Characteristics (Per SiC Diode)

The following table lists the SiC diode ratings and characteristics of the MSCSM70VR1M10CTPAG device.

**Table 1-5. SiC Diode Ratings and Characteristics**

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{RRM}$	Peak repetitive reverse voltage		—	—	1200	V	
$I_{RM}$	Reverse leakage current	$V_R = 1200V$	$T_J = 25\text{ }^\circ\text{C}$	—	30	400	$\mu\text{A}$
			$T_J = 175\text{ }^\circ\text{C}$	—	500	—	
$I_F$	DC Forward current						
$V_F$	Diode forward voltage	$I_F = 100A$	$T_J = 25\text{ }^\circ\text{C}$	—	1.5	1.8	V
			$T_J = 175\text{ }^\circ\text{C}$	—	2.1	—	
$Q_C$	Total capacitive charge	$V_R = 600V$	—	448	—	nC	
C	Total capacitance	$f = 1\text{ MHz}, V_R = 400V$	—	492	—	pF	
		$f = 1\text{ MHz}, V_R = 800V$	—	364	—		
$R_{thJC}$	Junction-to-case thermal resistance		—	—	0.304	$^\circ\text{C/W}$	

### 1.3 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the MSCSM70VR1M10CTPAG device.

**Table 1-6. Thermal and Package Characteristics**

Symbol	Characteristic	Min.	Max.	Unit		
V <sub>ISOL</sub>	RMS isolation voltage, any terminal to case t = 1 min, 50 Hz/60 Hz	4000	—	V		
T <sub>J</sub>	Operating junction temperature range	−40	175	°C		
T <sub>JOP</sub>	Recommended junction temperature under switching conditions	−40	T <sub>Jmax</sub> −25			
T <sub>STG</sub>	Storage case temperature	−40	125			
T <sub>C</sub>	Operating case temperature	−40	125			
Torque	Mounting torque	To heatsink	M6	3	5	N.m
Wt	Package weight	—	250			g

The following table lists the temperature sensor NTC of the MSCSM70VR1M10CTPAG device.

**Table 1-7. Temperature Sensor NTC**

Symbol	Characteristic	Min.	Typ.	Max.	Unit	
R <sub>25</sub>	Resistance at 25 °C	—	50	—	kΩ	
ΔR <sub>25</sub> /R <sub>25</sub>	—	—	5	—	%	
B <sub>25/85</sub>	T <sub>25</sub> = 298.15K	—	3952	—	K	
ΔB/B	—	T <sub>C</sub> = 100 °C	—	4	—	%

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T} - \frac{1}{T_{25}}\right)\right]}$$

T: Thermistor temperature  
R<sub>T</sub>: Thermistor value at T

**Note:** See [APT0406—Using NTC Temperature Sensor Integrated into Power Module](#) for more information.

### 1.4 Typical SiC MOSFET Performance Curve

The following figures show the SiC MOSFET performance curves of the MSCSM70VR1M10CTPAG device.

Figure 1-1. Maximum Thermal Impedance

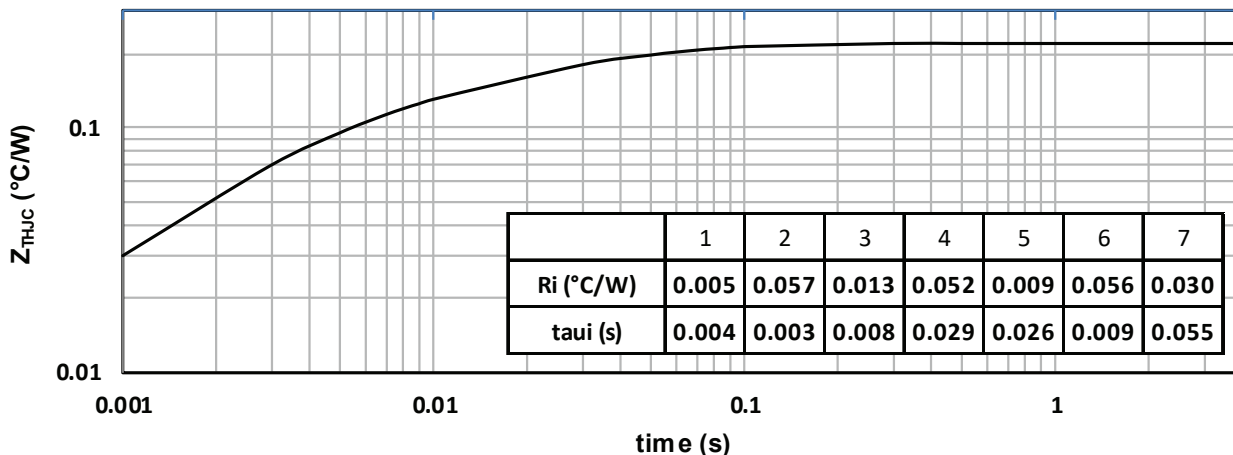


Figure 1-2. Output Characteristics,  $T_J = 25^\circ\text{C}$

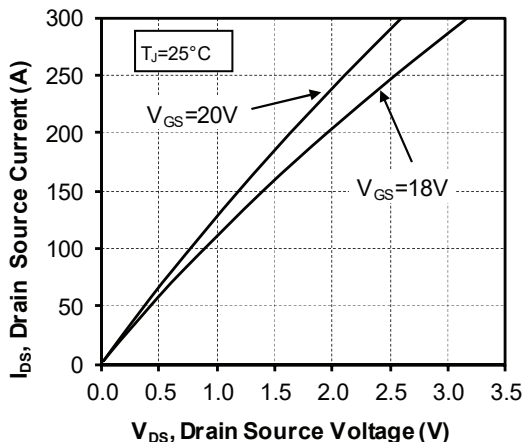


Figure 1-3. Output Characteristics,  $T_J = 175^\circ\text{C}$

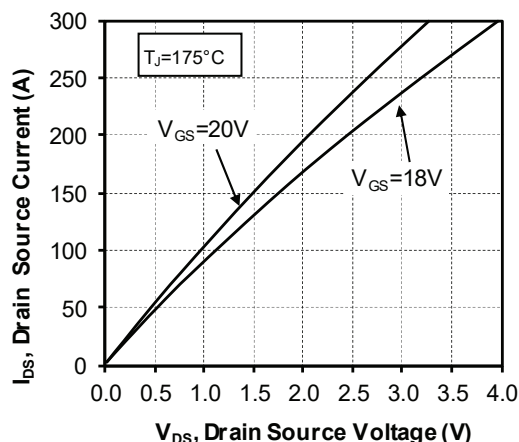


Figure 1-4. Normalized  $R_{DS(on)}$  vs. Temperature

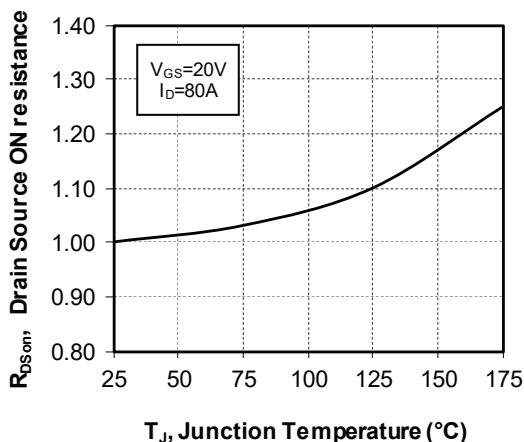
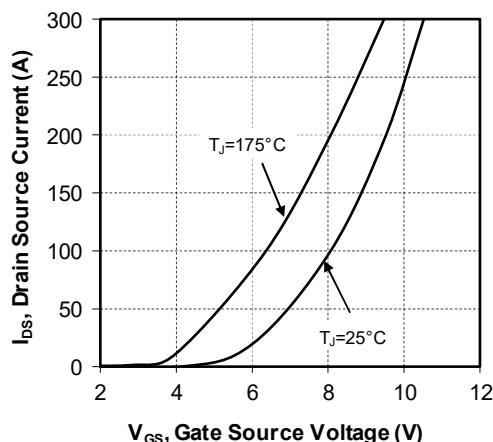


Figure 1-5. Transfer Characteristics



# MSCSM70VR1M10CTPAG

## Electrical Specifications

Figure 1-6. Switching Energy vs. Current

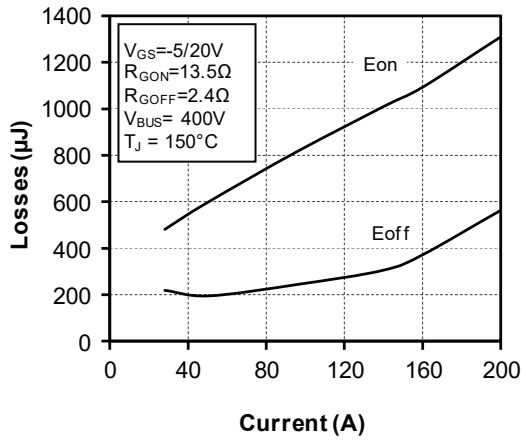


Figure 1-7. Turn On Energy vs.  $R_g$

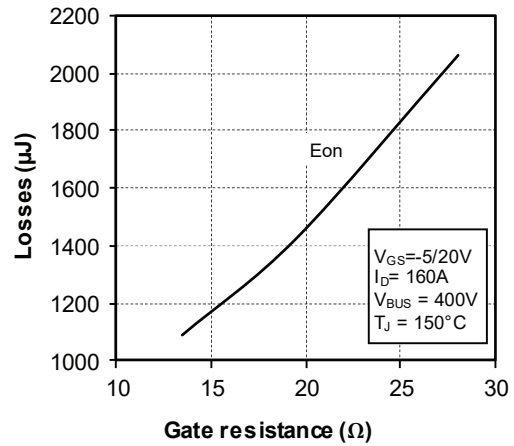


Figure 1-8. Capacitance vs. Drain Source Voltage

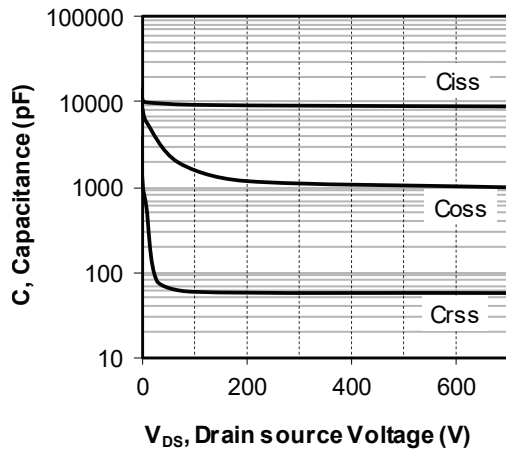


Figure 1-9. Gate Charge vs. Gate Source Voltage

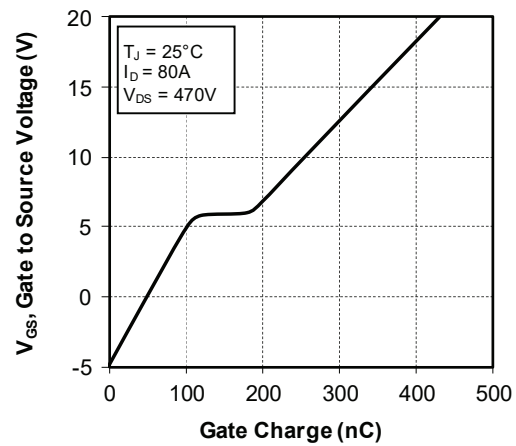


Figure 1-10. Body Diode Characteristics,  $T_J = 25^\circ\text{C}$

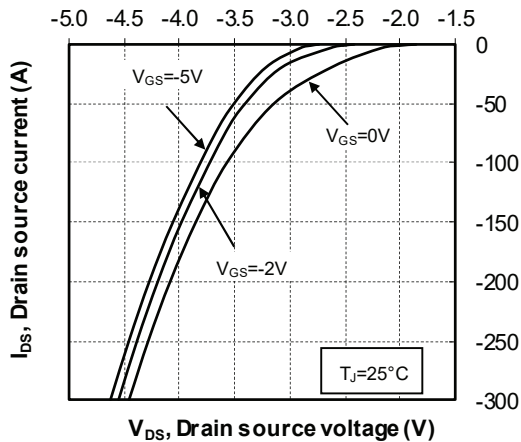
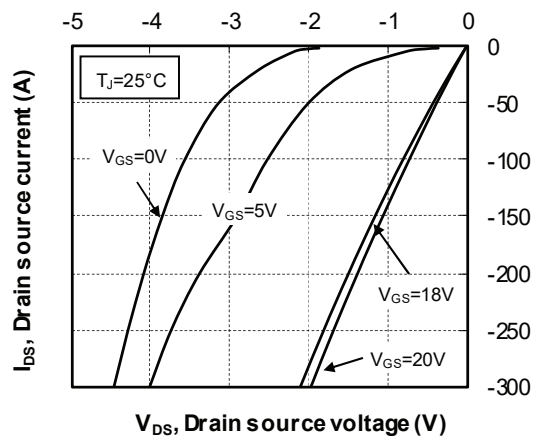


Figure 1-11. 3<sup>rd</sup> Quadrant Characteristics,  $T_J = 25^\circ\text{C}$





# MSCSM70VR1M10CTPAG

## Electrical Specifications

Figure 1-12. Body Diode Characteristics,  $T_J = 175^\circ\text{C}$

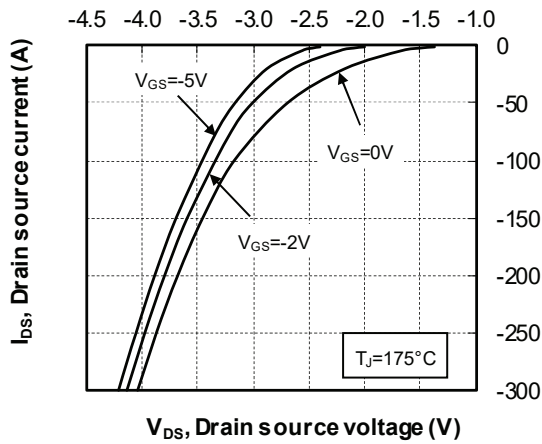


Figure 1-13. 3<sup>rd</sup> Quadrant Characteristics,  $T_J = 175^\circ\text{C}$

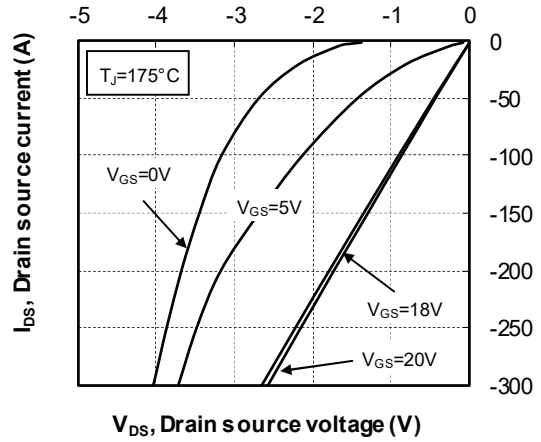


Figure 1-14. Operating Frequency vs Drain Current

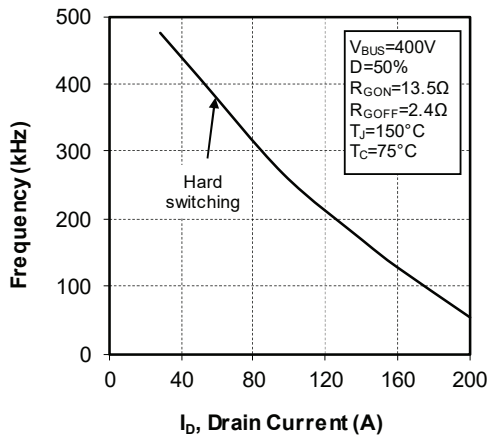
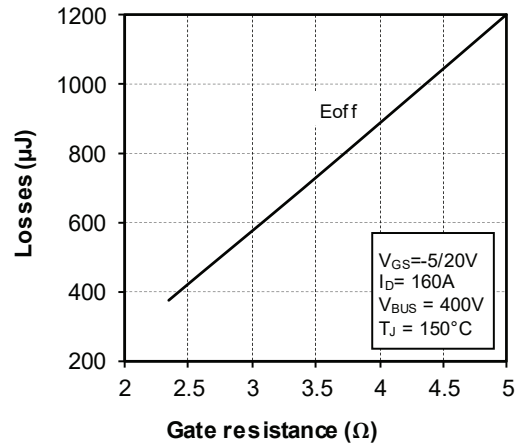


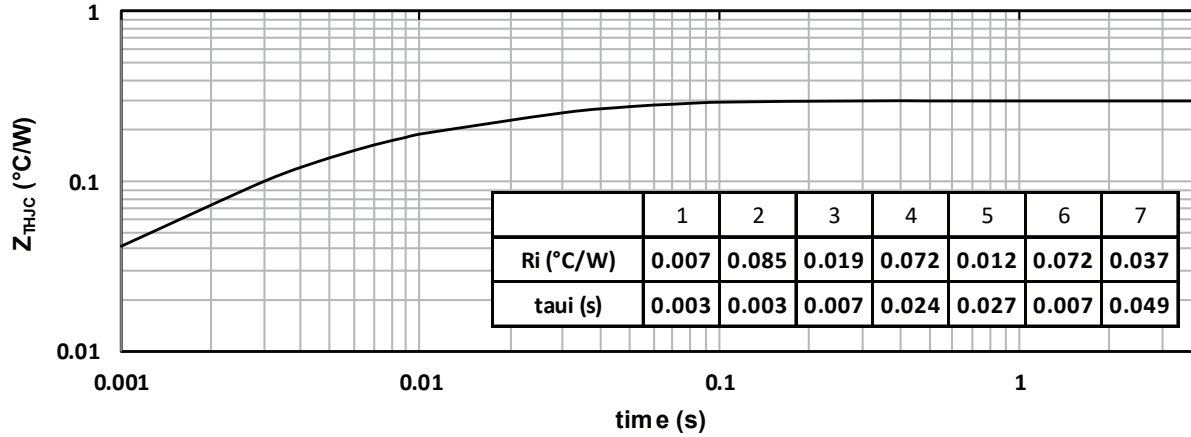
Figure 1-15. Turn Off Energy vs. Rg



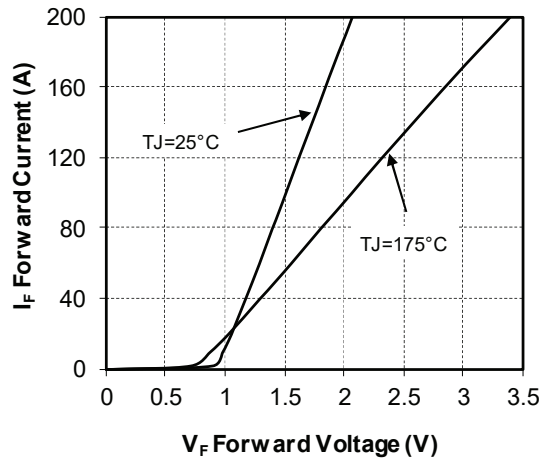
### 1.5 Typical SiC Diode Performance Curve

The following figures show the SiC diode performance curves of the MSCSM70VR1M10CTPAG device.

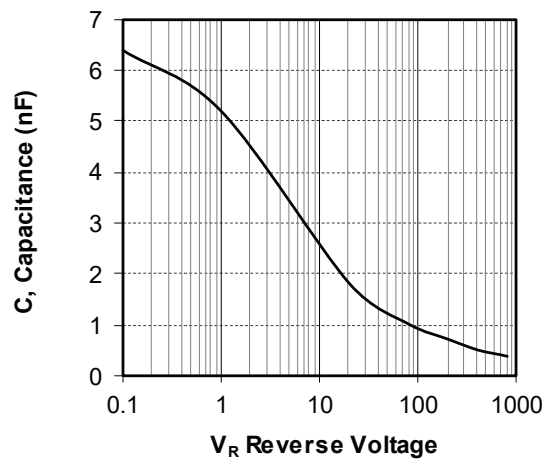
**Figure 1-16. Maximum Thermal Impedance**



**Figure 1-17. Forward Characteristics**



**Figure 1-18. Capacitance vs. Reverse Voltage**



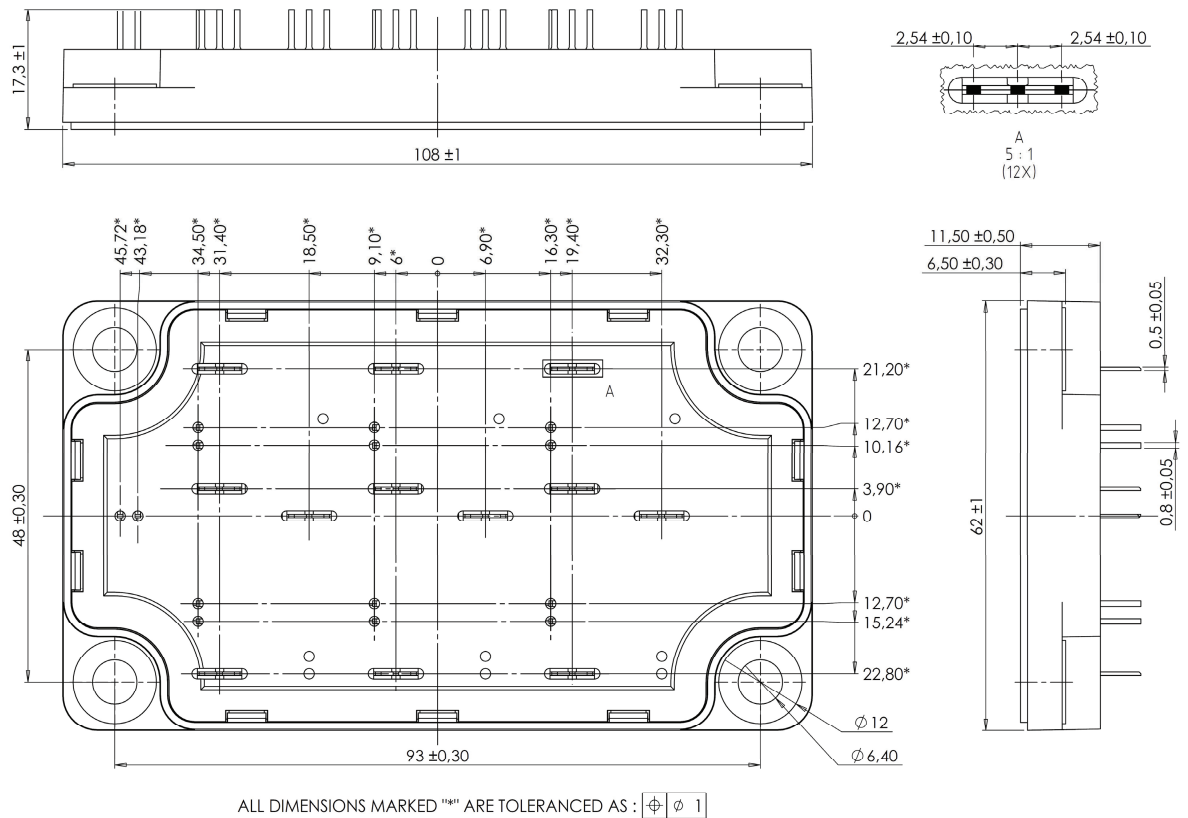
## 2. Package Specifications

The following section shows the package specification of the MSCSM70VR1M10CTPAG device.

### 2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM70VR1M10CTPAG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



**Note:** See [1902—Mounting Instructions for SP6-P \(12 mm\) Power Modules](#) for more information.

**3. Revision History**

Revision	Date	Description
A	08/2022	Initial Revision

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